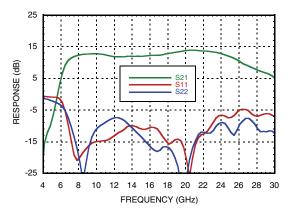


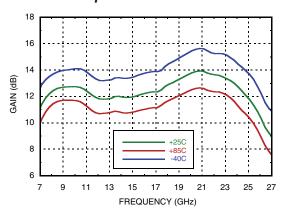


GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 7.5 - 26.5 GHz

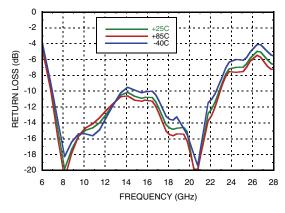
Broadband Gain & Return Loss



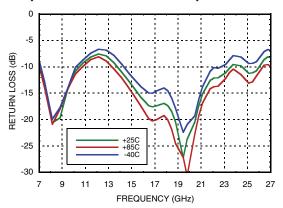
Gain vs. Temperature



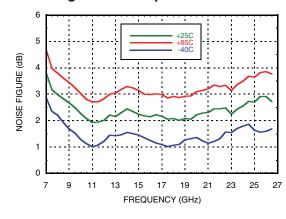
Input Return Loss vs. Temperature



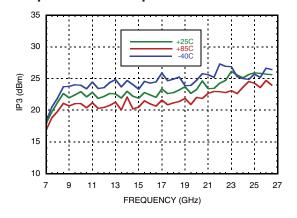
Output Return Loss vs. Temperature



Noise Figure vs. Temperature [1]



Output IP3 vs. Temperature



[1] Board loss subtracted out.

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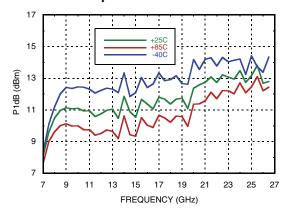
For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106 Phone: 781-329-4700 • Order online at www.analog.com Application Support: Phone: 1-800-ANALOG-D



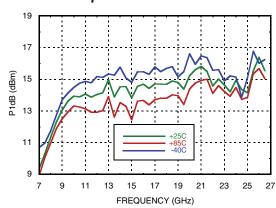


GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 7.5 - 26.5 GHz

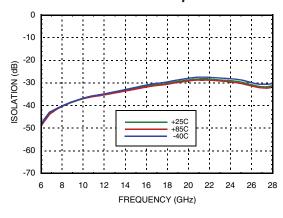
P1dB vs. Temperature



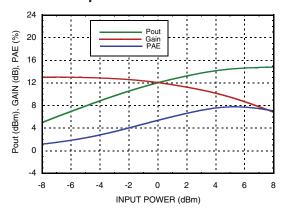
Psat vs. Temperature



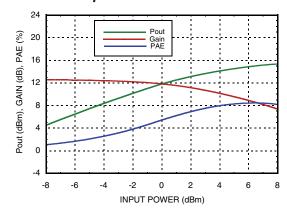
Reverse Isolation vs. Temperature



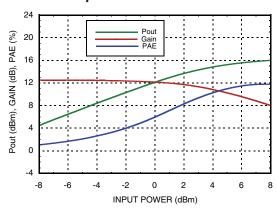
Power Compression @ 10 GHz



Power Compression @ 17 GHz



Power Compression @ 24 GHz

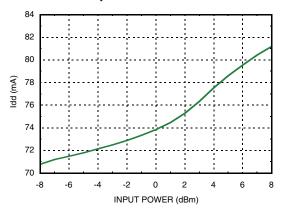






GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 7.5 - 26.5 GHz

Current vs. Input Power @ 17 GHz



Absolute Maximum Ratings

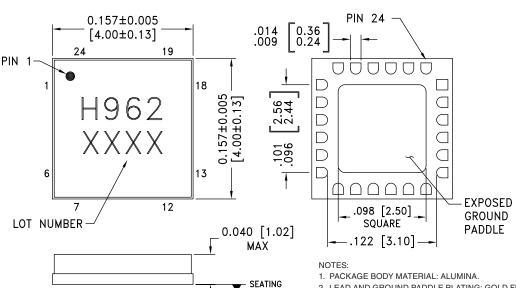
| rain Bias Voltage +4V | | |
|---|----------------|--|
| RF Input Power | +10 dBm | |
| Channel Temperature | 150 °C | |
| Continuous Pdiss (T = 85 °C) (derate 5.97 mW/°C above 85 °C) | 0.39 W | |
| Thermal Resistance (Channel to ground paddle) | 167.6 °C/W | |
| Storage Temperature | -65 to +150 °C | |
| Operating Temperature | -40 to +85 °C | |
| ESD Sensitivity (HBM) | Class 1A | |



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing

BOTTOM VIEW



PLANE

C-

- 2. LEAD AND GROUND PADDLE PLATING: GOLD FLASH OVER NICKEL.
- 3. DIMENSIONS ARE IN INCHES (MILLIMETERS).
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05MM DATUM C -
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking [2] |
|-------------|-----------------------|------------------|---------------------|---------------------|
| HMC962LC4 | Alumina, White | Gold over Nickel | MSL3 ^[1] | H962 XXXX |

^[1] Max peak reflow temperature of 260 $^{\circ}\text{C}$

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^{[2] 4-}Digit lot number XXXX



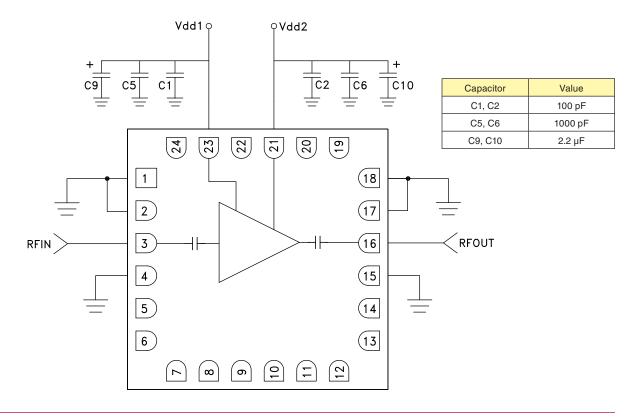


GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 7.5 - 26.5 GHz

Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|---------------------------|------------|--|---------------------|
| 1, 2, 4, 15, 17, 18 | GND | These pins and package bottom must be connected to RF/DC ground. | GND = |
| 3 | RFIN | This pin AC coupled and matched to 50 Ohms | RFIN O— |
| 5 - 14, 19, 20, 22, 24 | N/C | No connection necessary. These pins may be connected to RF/DC ground. Performance will not be affected. | |
| 16 | RFOUT | This pin AC coupled and matched to 50 Ohms | RFOUT |
| 21, 23 | Vdd1, Vdd2 | Power supply voltages for the amplifier. Bypass capacitors are required. See application circuit herein. | Vdd1,2 |

Application Circuit



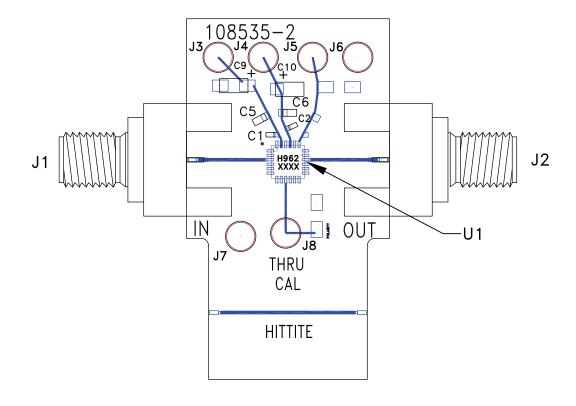
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GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 7.5 - 26.5 GHz

Evaluation PCB



List of Material for Evaluation PCB EVAL01-HMC962LC4 [1]

| Item | Description |
|---------|------------------------------|
| J1, J2 | 2.92 mm Connectors |
| J3 - J8 | DC Pin |
| C1, C2 | 100 pF Capacitor, 0402 Pkg. |
| C5, C6 | 1000 pF Capacitor, 0603 Pkg. |
| C9, C10 | 2.2 µF Capacitor, Tantalum |
| U1 | HMC962LC4 Amplifier |
| PCB [2] | 108535 Evaluation PCB |

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

^[2] Circuit Board Material: Rogers 4350 or Arlon 25FR